



November 2007
UniFET™

FDB12N50F

N-Channel MOSFET, FRFET

500V, 11.5A, 0.7Ω

Features

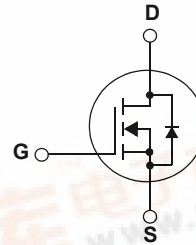
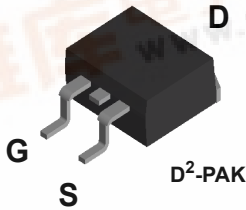
- $R_{DS(on)} = 0.59\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 6A$
- Low gate charge (Typ. 21nC)
- Low C_{rss} (Typ. 11pF)
- Fast switching
- 100% avalanche tested
- Improve dv/dt capability
- RoHS compliant



Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advance technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switching mode power supplies and active power factor correction.



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

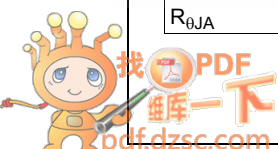
Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	500	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	-Continuous ($T_C = 25^\circ\text{C}$)	11.5
		-Continuous ($T_C = 100^\circ\text{C}$)	6.9
I_{DM}	Drain Current	- Pulsed (Note 1)	46
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	456
I_{AR}	Avalanche Current	(Note 1)	11.5
E_{AR}	Repetitive Avalanche Energy	(Note 1)	16.5
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	165
		- Derate above 25°C	1.33
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.75	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

FDB12N50F N-Channel MOSFET



Package Marking and Ordering Information $T_C = 25^\circ\text{C}$ unless otherwise noted

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB12N50F	FDB12N50FTM_WS	D2-PAK	330mm	24mm	800

Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	500	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, Referenced to 25°C	-	0.5	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 400\text{V}, T_C = 125^\circ\text{C}$	-	-	10 100	μA
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 6\text{A}$	-	0.59	0.7	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{V}, I_D = 6\text{A}$ (Note 4)	-	12	-	S

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$	-	1050	1395	pF
C_{OSS}	Output Capacitance		-	135	180	pF
C_{RSS}	Reverse Transfer Capacitance		-	11	17	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 400\text{V}, I_D = 11.5\text{A}$ $V_{GS} = 10\text{V}$ (Note 4, 5)	-	21	30	nC
Q_{gs}	Gate to Source Gate Charge		-	6	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	9	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{V}, I_D = 11.5\text{A}$ $R_G = 25\Omega$ (Note 4, 5)	-	21	50	ns
t_r	Turn-On Rise Time		-	45	100	ns
$t_{d(off)}$	Turn-Off Delay Time		-	50	110	ns
t_f	Turn-Off Fall Time		-	35	80	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	11.5	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	46	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 11.5\text{A}$	-	-	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_{SD} = 11.5\text{A}$	-	134	-	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4)	-	0.37	-	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 6.9\text{mH}, I_{AS} = 11.5\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 11.5\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

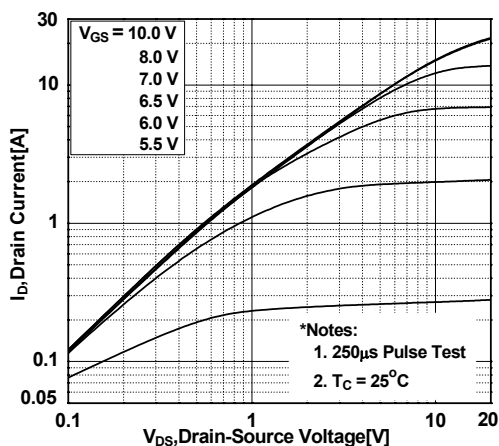


Figure 2. Transfer Characteristics

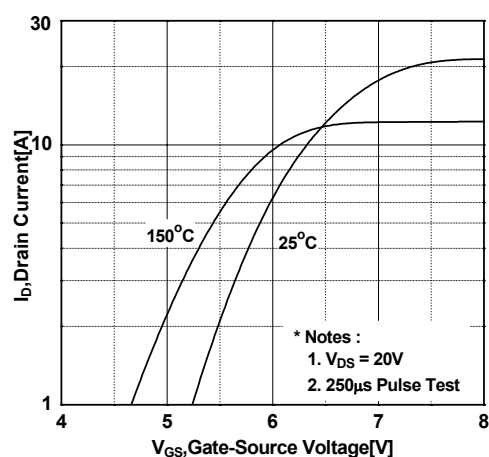


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

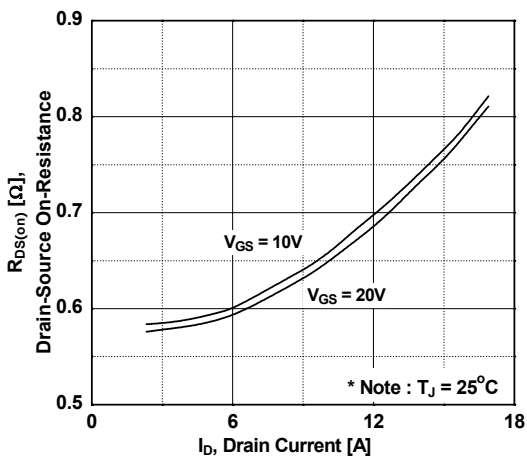


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

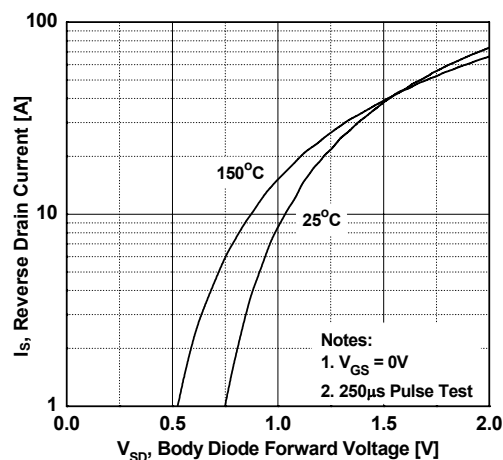


Figure 5. Capacitance Characteristics

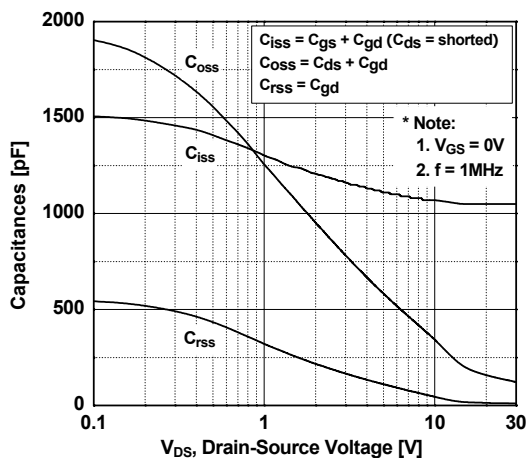
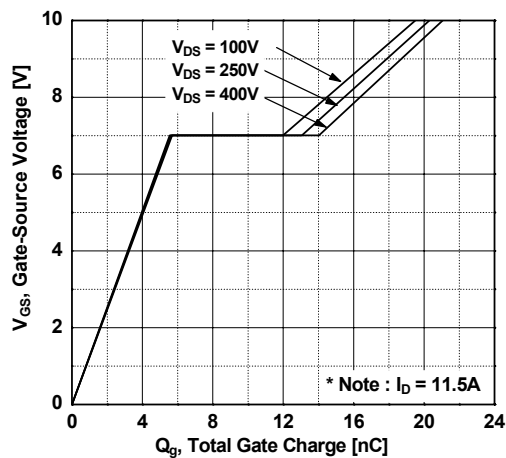


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

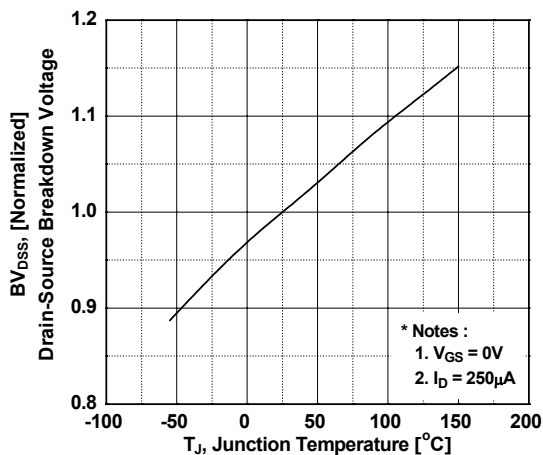


Figure 8. Maximum Safe Operating Area

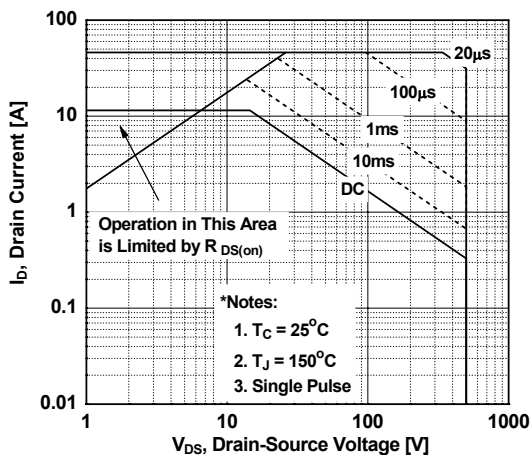


Figure 10. Maximum Drain Current vs. Case Temperature

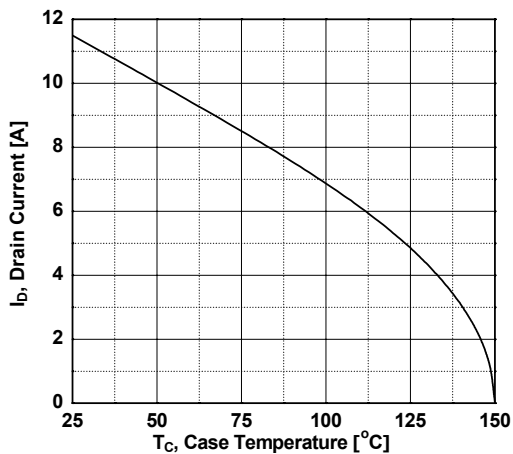
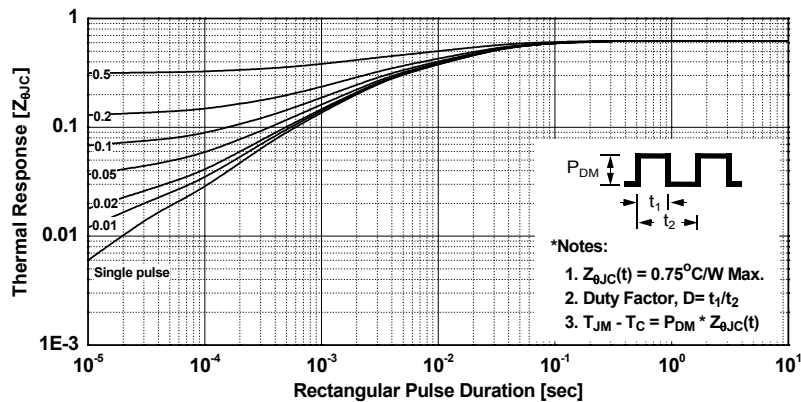
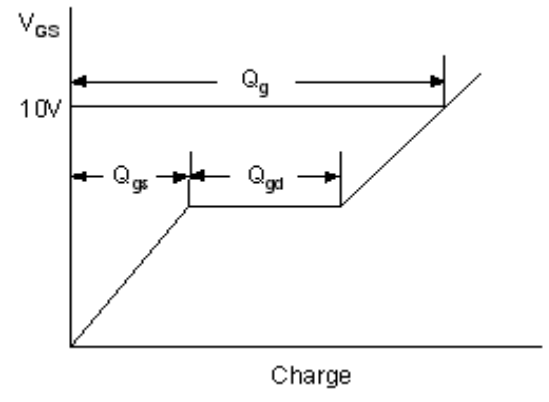
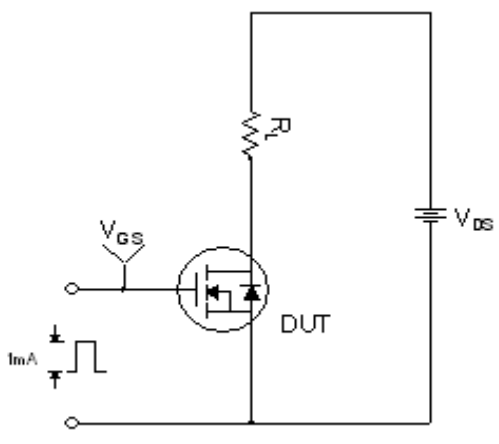


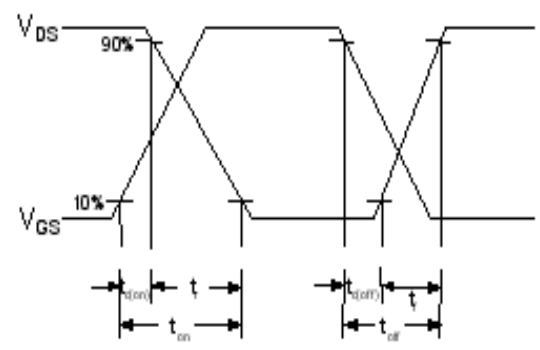
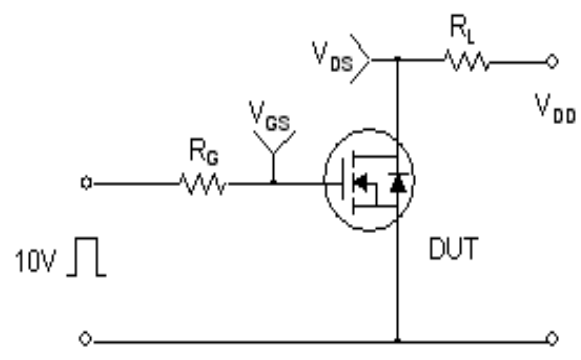
Figure 11. Transient Thermal Response Curve



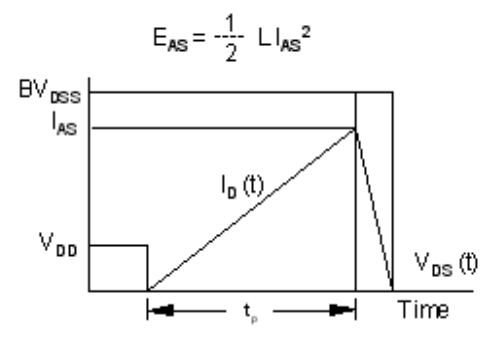
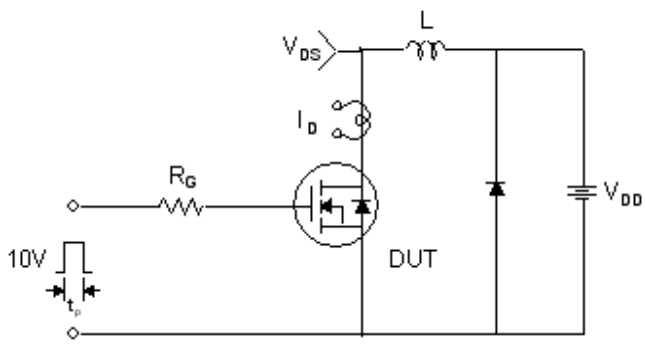
Gate Charge Test Circuit & Waveform



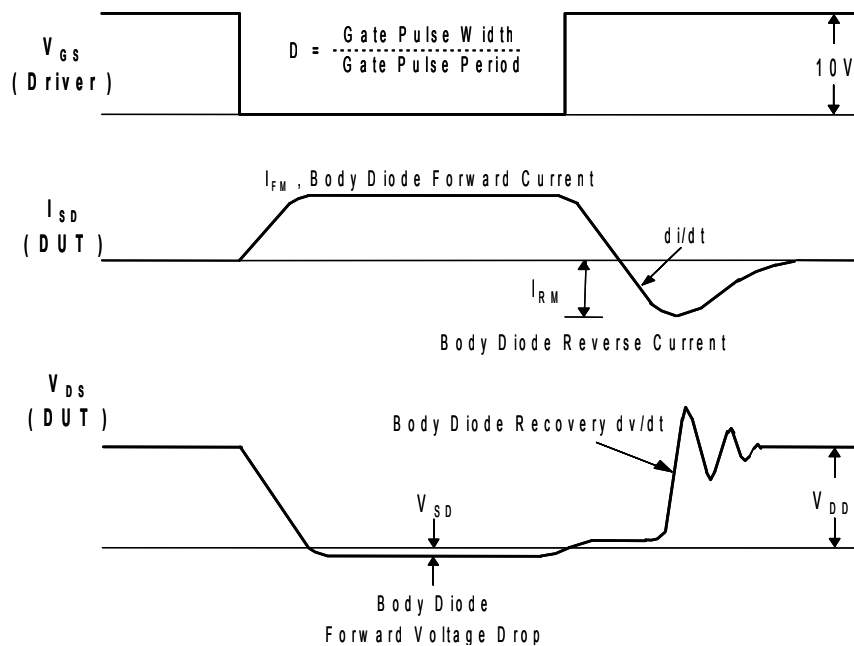
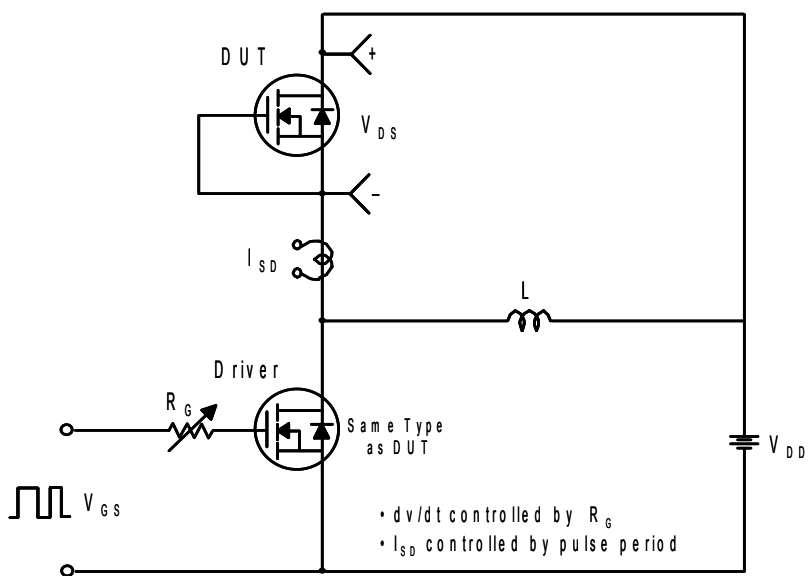
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

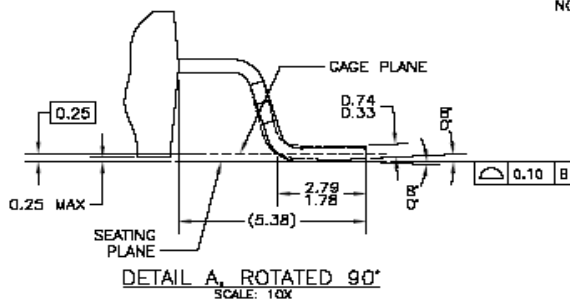
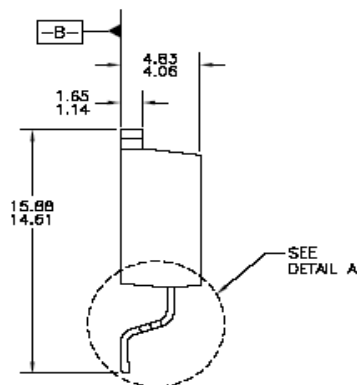
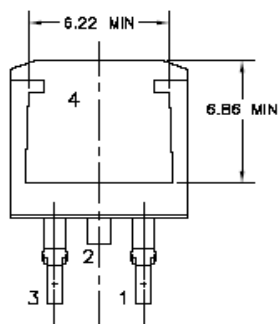
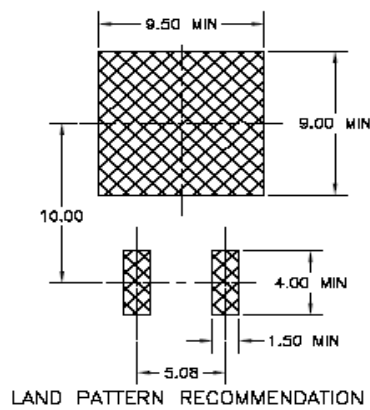
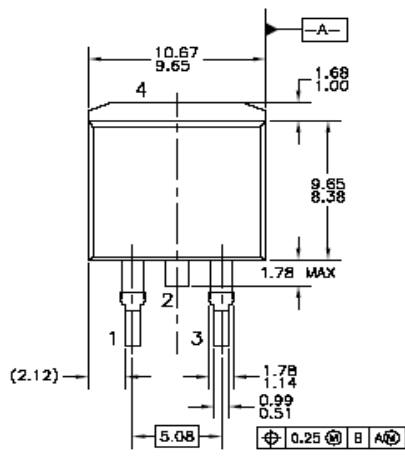


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

D2-PAK



- NOTES: UNLESS OTHERWISE SPECIFIED
 A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) REFERENCE JEDEC, TO-263, ISSUE D, VARIATION AB, DATED JULY 2003.
 C) DIMENSIONING AND TOLERANCING PER ANSI Y14.5M - 1982.
 D) LOCATION OF THE PIN HOLE MAY VARY (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE).
 E) PRESENCE OF TRIMMED CENTER LEAD IS OPTIONAL.


T02B3AD2REVD

Dimensions in Millimeters



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